

## SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

**Monolithic Digital IC** 

# LB11873 — For Polygonal Mirror Motors Three-Phase Brushless Motor Driver

## Overview

The LB11873 is a 3-phase brushless motor driver developed for driving the polygonal mirror motor used in plain-paper copiers and similar products. This IC can implement the circuits required for polygonal mirror motor drive (speed control and driver circuits) in a single chip.

The LB11873 implements low-noise/low-vibration PWM drive by changing the current at phase switching gradually to reduce motor noise.

#### **Functions**

- Three-phase bipolar drive (quiet direct PWM)
- PLL speed control circuit
- Hall sensor FG support
- Dedicated external clock
- Brake mode switching circuit (free running and reverse braking)
- Phase lock detection output (with masking function)
- Built-in current limiter, constraint protection, undervoltage protection, thermal protection, and CLK line disconnection protection circuits
- Input pins support 3V system microcontrollers

## **Specifications**

## **Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V <sub>CC</sub> max		30	V
Output current	I <sub>O</sub> max	T ≤ 500ms	1.8	Α
Allowable power dissipation 1	Pd max1	Independent IC	0.9	W
Allowable power dissipation 2	Pd max2	When mounted on a circuit board *1	2.1	W

<sup>\*1</sup> Specified circuit board :  $114.3 \times 76.1 \times 1.6 \text{mm}^3$ , glass epoxy.

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Parameter	Symbol	Conditions	Ratings	Unit
Operating temperature	Topr		-20 to +80	°C
Storage temperature	Tstg		-55 to +150	°C

## Allowable Operating Ranges at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage range	V <sub>CC</sub>		9.5 to 28	V
5V constant voltage output	IREG		0 to -30	mA
LD pin apply voltage	VLD		0 to 28	V
LD pin output current	ILD		0 to 15	mA
FGS pin apply voltage	VFGS		0 to 28	V
FGS pin output current	IFGS		0 to 10	mA
HB pin apply voltage	VHBS		0 to 28	V
HB pin output current	IHBS		0 to 30	mA

## Electrical Characteristics at $Ta=25^{\circ}C,\ V_{CC}=V_{M}=24V$

Parameter	Symbol Conditions	Conditions		Ratings		Unit
Faranietei	Symbol	Conditions	min	typ	max	Offic
Supply current 1	I <sub>CC</sub> 1			22	28	mA
Supply current 2	I <sub>CC</sub> 2	Stop mode		4.0	6.0	mA
5V constant voltage output (VRI	EG pin)					
Output voltage	VREG		4.65	5.0	5.35	V
Line regulation	ΔVREG1	V <sub>CC</sub> = 9.5 to 28V		80	130	mV
Load regulation	ΔVREG2	I <sub>O</sub> = -5 to -20mA		10	60	mV
Temperature coefficient	ΔVREG3	Design target*		0		mV/°C
Output Block						
Output saturation voltage 1	V <sub>O</sub> sat1	$I_O = 0.5A$ , $V_O$ (sink) + $V_O$ (source)		1.4	1.9	V
Output saturation voltage 2	V <sub>O</sub> sat2	$I_O = 1.2A$ , $V_O (sink) + V_O (source)$		2.0	2.6	V
Output leakage current	l <sub>O</sub> leak				100	μΑ
High side diode forward voltage 1	VD2-1	ID = 0.5A		1.0	1.5	V
High side diode forward voltage 2	VD2-2	ID = 1.2A		1.5	2.0	V
Hall Sensor Amplifier Block			•	•		
Input bias current	IHB			2	10	μА
Differential input range	VIHIN	Sine wave input	50		350	
Common-mode input voltage	VICM		1.5		VREG –	V
range					1.0	
Input offset voltage	VIOH	Design target value*	-20		20	mV
Hall Sensor Bias	1					
Output saturation voltage	V <sub>OL</sub> (HB)	IHB = 10mA	1.5		2.0	V
Output leakage current	I <sub>L</sub> (HB)	$V_O = V_{CC}$ , stop mode			10	μΑ
FG Schmitt Trigger Block (IN1)						
Input amplifier gain	GFG	Design target value*		5		Times
Input hysteresis (high $\rightarrow$ low)	VSHL	Design target value*		0		mV
Input hysteresis (low $\rightarrow$ high)	VSLH	Design target value*		-10		mV
Hysteresis	VFGL	Input conversion, design target value *	4	7	12	mV
PWM Oscillator						
High-level output voltage	V <sub>OH</sub> (PWM)		2.65	2.95	3.25	V
Low-level output voltage	V <sub>OL</sub> (PWM)		0.9	1.2	1.5	V
External capacitor charge current	ICHG	VPWM = 2V	-60	-45	-30	μА
Oscillator frequency	f (PWM)	C = 680pF		34		kHz
Amplitude	V (PWM)		1.45	1.75	2.05	Vp-p

 $<sup>^{\</sup>star}$  The design specification items are design guarantees and are not measured.

Continued from preceding page.				Ratings		Unit
Parameter	Symbol	Conditions	min	_	may	Offic
FGS Pin			111111	typ	max	
Output saturation voltage	V <sub>OL</sub> (FGS)	IFGS = 7mA		0.15	0.5	V
Output leakage current	I <sub>L</sub> (FGS)			0.15	0.5	
CSD Oscillator Circuit	IL (1 GG)	VO = VCC			10	μΑ
	£ (CCD)	C 0.022F		31		11-
Oscillator frequency	f (CSD)	C = 0.033μF		-		Hz
High-level output voltage	V <sub>OH</sub> (CSD)		3.50	3.75	4.00	V
Low-level output voltage	V <sub>OL</sub> (CSD)		1.00	1.30	1.60	V
Amplitude	V (CSD)		2.20	2.45	2.80	Vp-p
External capacitor charge current	ICHG1	VCSD = 2V	-7	-5	-3	μА
External capacitor discharge current	ICHG2	VCSD = 2V	3	5	7	μΑ
Lock detection delay counts	CSDCT1			7		
Clock disconnected protection counts	CSDCT2			2		
Constraint protection operation counts	CSDCT3			31		
Initial reset voltage	VRES			0.6	0.8	V
Phase Comparator Output	1 11120	<u> </u>		0.0	0.0	•
High-level input voltage	VPDH	I <sub>OH</sub> = -100μA	VREG - 0.2	VREG - 0.1		V
Low-level input voltage	VPDL	I <sub>OL</sub> = 100μA	VREG - 0.2	0.2	0.3	
Input source current	IPD+	VPD = VREG/2		0.2	-0.5	mA
•			1.5		-0.3	mA
Input sink current IPD- VPD = VREG/2 1.5						MA
Phase Lock Detection Output	\/ ((D)	10774				
Output saturation voltage	V <sub>OL</sub> (LD)	I <sub>LD</sub> = 10mA		0.15	0.5	V
Output leakage current	I <sub>L</sub> (LD)	AO = ACC			10	μΑ
Error Amplifier Block	\/ (ED)	I Button and the				
Input offset voltage	V <sub>IO</sub> (ER)	Design target value*	-10		10	mV
Input bias current	IB (ER)		-1		1	μΑ
High-level output voltage	V <sub>OH</sub> (ER)	IEI = -0.1mA, no load	3.7	4.0	4.3	V
Low-level output voltage	V <sub>OL</sub> (ER)	IEI = 0.1mA, no load	0.7	1.0	1.3	V
DC bias level	VB (ER)		-5%	VREG/2	5%	V
Current Llimiter Circuit	Г	1				
Drive gain 1	GDF1	In the phase locked state	0.4	0.5	0.6	Times
Drive gain 2	GDF2	In the unlocked state	0.8	1.0	1.2	Times
Llimiter voltage 1	VRF1	V <sub>CC</sub> - VM, forward mode	0.45	0.5	0.55	V
Llimiter voltage 2	VRF2	V <sub>CC</sub> - VM, reverse mode	0.225	0.25	0.275	V
Thermal shutdown circuit						
Thermal shutdown operating temperature	TSD	Design target value* (junction temperature)	150	170		°C
Thermal shutdown temperature hysteresis	ΔTSD	Design target value* (junction temperature)		40		°C
Low Voltage Protection Circuit	<u> </u>	comperatore)				
Operating voltage	VSDL		8.1	8.45	8.9	V
Hysteresis	ΔVSD		0.2	0.35	0.5	V
CLK pin	<u> </u>	1	I	<u> </u>		
External input frequency	fl (CLK)		0.1		10	kHz
High-level input voltage	V <sub>IH</sub> (CLK)		2.0		VREG	V
Low-level input voltage	V <sub>IL</sub> (CLK)		0		1.0	V
Input open voltage	VIC (CLK)		<del>-</del>	3.0	1.0	V
Hysteresis	VIO (CLK) VIS (CLK)					
High-level input current	I <sub>IH</sub> (CLK)	VCKIN = VREG		0.25	150	μA
Low-level input current	I <sub>IL</sub> (CLK)	VCKIN = VKEG	200	115	150	μΑ
Low-level input curiefit	IIL (CLK)	V OININ - UV	-220	-175	Continued of	

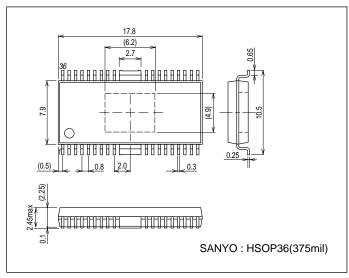
Note : \* The design specification items are design guarantees and are not measured.

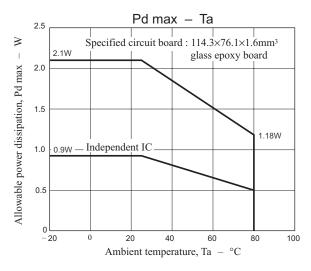
Parameter	Symbol Conditions	Ratings			Unit	
Faiametei	Symbol	Symbol Conditions	min	typ	max	
S/S pin			<u>.</u>	•		
High-level input voltage	V <sub>IH</sub> (SS)		2.0		VREG	V
Low-level input voltage	V <sub>IL</sub> (SS)		0		1.0	V
Input open voltage	VIO (SS)			3.0		V
Hysteresis	VIS (SS)		0.21	0.25	0.29	V
High-level input current	I <sub>IH</sub> (SS)	VS/S = VREG		115	150	μΑ
Low-level input current	I <sub>IL</sub> (SS)	VS/S = 0V	-220	-175		μΑ
BRSEL pin						
High-level input voltage	V <sub>IH</sub> (BRSEL)		2.0		VREG	V
Low-level input voltage	V <sub>IL</sub> (BRSEL)		0		1.0	V
Input open voltage	VIO (BRSEL)			3.0		V
Hysteresis	VIS (BRSEL)		0.21	0.25	0.29	V
High-level input current	I <sub>IH</sub> (BRSEL)	VBRSEL = VREG		115	150	μΑ
Low-level input current	I <sub>IL</sub> (BRSEL)	VBRSEL = 0V	-220	-175		μΑ

## **Package Dimensions**

unit: mm (typ)

3235A





## Three-Phase Logic Truth Table (The input "H" state is the state where IN+ > IN-)

	· · · · · · · · · · · · · · · · · · ·				
IN1	IN2	IN3	OUT1	OUT2	OUT3
Н	L	Н	L	Н	M
Н	L	L	L	M	Н
Н	Н	L	M	L	Н
L	Н	L	Н	L	М
L	Н	Н	Н	M	L
L	L	Н	М	Н	L

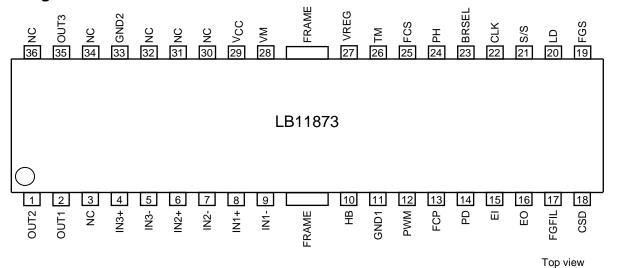
S/S pin

C, C p					
Input state	State				
High or open	Stop				
Low	Start				

## BRESEL pin

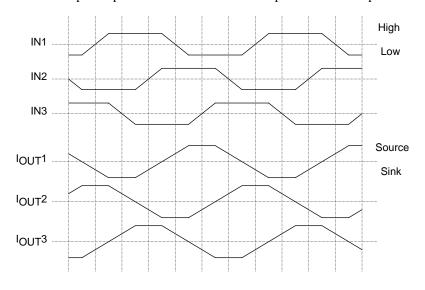
Input state	During deceleration	
High or open	Free running	
Low	Reverse braking	

## **Pin Assignment**



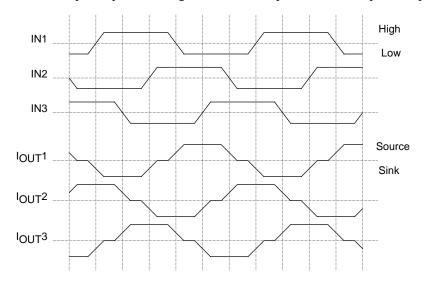
## Hall sensor input waveforms and output current waveform

(1) When the Hall sensor input amplitude is small or when the input waveform slope is low



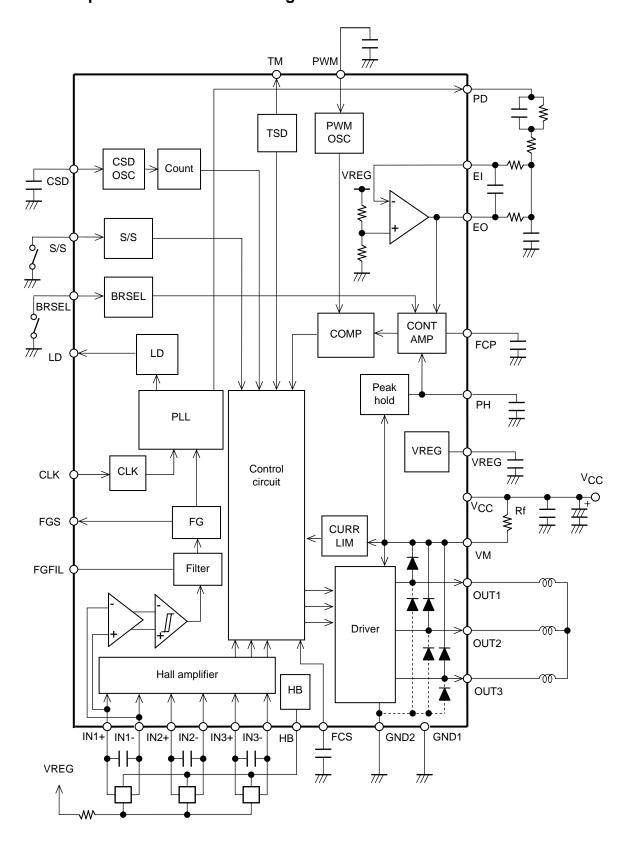
180° drive: Current flows during all periods; there are on off periods (180° drive)

(2) When the Hall sensor input amplitude is larger or when the input waveform slope is steep

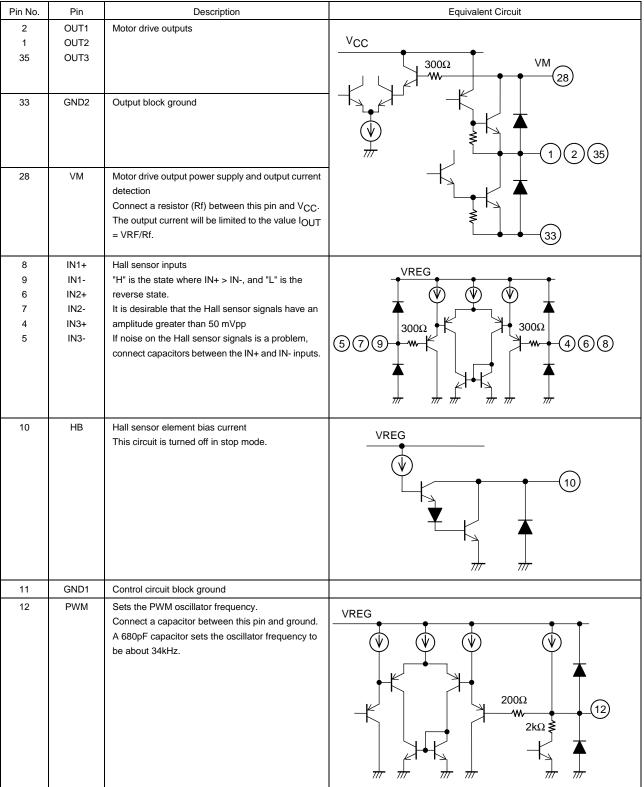


In this case, periods in which drive is off will occur (the off periods vary depending on the Hall sensor inputs).

## Internal Equivalent Circuit Block Diagram and External Reference Circuit



## **Pin Functions**



	om preceding j		
Pin No.	Pin	Description	Equivalent Circuit
13	FCP	Current limiter circuit frequency characteristics correction  Connect a capacitor (about 0.01µF to 0.1µF) between this pin and ground.  The output duty is determined by comparing the voltage at this pin with the PWM oscillator waveform.	VREG  300Ω  13
14	PD	Phase comparator output The phase error is converted to a pulse duty and output from this pin.	VREG 300Ω 14
15	EI	Error amplifier input	VREG (V) (V) (V) (V) (T) (T) (T) (T) (T) (T) (T) (T) (T) (T
16	EO	Error amplifier output	VREG 16 16 16
17	FGFIL	FG filter This pin is normally left open. If noise on the FG signal is a problem, connect a capacitor (about 20pF or smaller) between this pin and ground.	VREG  300Ω  17  Continued on next page.

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Pin No.	Pin	Description	Equivalent Circuit
18	CSD	Initial reset pulse generation and protection circuit reference oscillator Connect a capacitor between this pin and ground.	VREG    18   18   18   18   18   18   18   1
19	FGS	FG Schmitt trigger output	VREG (19)
20	LD	Phase lock detection output This output goes to the on state (low-level output) in the phase locked state.	VREG 20
21	S/S	Start/stop control Low: 0V to 1.0V High: 2.0V to VREG Hysteresis: about 0.25V This pin goes to the high level when open. A low level specifies the start state.	VREG  20kΩ ₹  5kΩ  30kΩ ₹  7// /// /// /// /// /// /// /// /// //
22	CLK	Clock input Low: 0V to 1.0V High: 2.0V to VREG Hysteresis: about 0.25V fCLK = 10kHz max. If there is noise on this signal, insert a noise rejection capacitor at this input.	VREG $20k\Omega$ $5k\Omega$ $30k\Omega$ Continued on next page.

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Pin No.	Pin	Description	Equivalent Circuit
23	BRSEL	Deceleration (braking) control selection Low: 0V to 1.0V High: 2.0V to VREG This pin goes to the high level when open. A low level selects reverse torque control and a high level selects free running braking. If reverse torque control is used, an external Schottky barrier diode will be required on the low side of the output.	VREG  20kΩ ₹  5kΩ  30kΩ ₹  777  777  777  777  777  777  777
24	PH	RF waveform smooth  Connect a capacitor between this pin and ground.	VREG 500Ω 34
25	FCS	Control loop frequency characteristics correction Connect a capacitor between this pin and ground.	VREG 300Ω 25
26	ТМ	Monitor output This pin is normally left open.	VREG  300Ω  300Ω  Continued on next page.

Pin No.	Pin	Description	Equivalent Circuit
27	VREG	Stabilized power supply output (5V output) Connect a capacitor between this pin and ground for power supply stabilization. (About 0.1μF)	VCC 277
29	Vcc	Power supply. Connect a capacitor (a few tens of μF or larger) between this pin and ground so that noise does not enter the IC.	
3, 30 31, 32 34, 36	NC	Since this pin is not connected internally to the chip, it can be used for wiring connections.	
,	FRAME	Connect this pin to ground.	

#### LB11873 Overview

#### 1. Speed control circuit

Since the LB11873 adopts PLL speed control, it provides precise, low-jitter, and stable motor operation. This PLL circuit compares the falling edge of the CLK signal with the FG signal (edges on which the IN1 input changes from low to high and FGS output rising edges) and controls motor operation based on the difference.

During control operation, the FG servo frequency is the same as the CLK signal frequency.

 $f_{FG}$  (servo) =  $f_{CLK}$ 

## 2. Output drive circuit

This IC minimizes motor vibration and noise by changing the output current smoothly during phase switching. Since the change (slope) imposed on the output current during phase switching uses the slope of the Hall sensor input waveform, the changes in the output waveforms at phase switching will become too steep if the Hall sensor input waveform slope is steep. This will reduce the noise and vibration reducing effect of this technique. Thus care is required concerning the slope of the Hall sensor input waveform.

Low side output transistor PWM switching is used for motor speed control and the drive output is adjusted by changing the duty. The diode between OUT and VM used for the regenerative current when the PWM is off is built into this IC. Due to the parasitic diode between OUT and ground, if reverse control mode (torque braking) is selected for braking, an external Schottky barrier diode must be used. Also, if there are problems when the output current is large (for example, incorrect operation or waveform disruption during low side kickback) a Schottky barrier diode must be connected between OUT and ground.

Note that if it is necessary to reduce IC thermal dissipation during constant-speed operation, it may be effective to insert a Schottky barrier diode between OUT and VM. This effect occurs because the regenerative current during PWM switching will be dissipated in the external diode instead of the IC's internal diode.

## 3. Current limiter circuit

The current limiter circuit limits the drive current to a current determined by the equation I = VRF/RF, where VRF = 0.5V (typical) and Rf is the current detection resistor. The limiting operation works by reducing other output on duty to suppress the drive current.

The current limiter circuit detects the reverse recovery current due to PWM operation and, to assure that the current limiting operation is not performed incorrectly, provides a delay of about 2µs before it operates. Since the changes in the current levels at startup (the state where there is no counterelectromotive force from the motor) will be rapid if either the motor coil resistance is low or if the inductance is low, there are cases where current limiter will operates at a current level above that set due to this delay. In these cases, it will be necessary to take the amount of current increase due to the delay into account when setting the current limit value.

#### 4. Power saving circuit

This IC goes into a power saving state in which current drain is reduced when set to the stop state. This power saving state is implemented by cutting the bias current to most of the circuits in the IC. The 5V regulator output, however, is still output when the IC is in the power saving state.

#### 5. Reference clock

Care must be taken to assure that no noise due to chattering or other problems appears on the externally input clock signal. While the input circuit is designed with hysteresis, noise must be rejected by, for example, inserting capacitors in the clock line if noise problems occur.

The LB11873 provides a built-in clock disconnection protection circuit. At clock frequencies lower than the frequency determined by the following equation, the LB11873 will not perform its normal control operation, but rather will operate in an intermittent mode.

 $f(Hz) \approx 1.02 \div CCSD$  CCSD ( $\mu F$ ): the capacitor connected between the CSD pin and ground.

If a 0.033µF capacitor is used, the frequency will be about 31Hz.

If the IC is set to the start state with absolutely no clock signal provided, the motor will first start to turn somewhat and then the drive will be turned off.

If motor rotation stops, a time in excess of the constraint protection operating time elapses, and then the clock signal is applied again, drive operation will not be restarted. However, if the clock signal is reapplied before the constraint protection circuit operates, drive operation will restart.

## 6. PWM frequency

The PWM frequency is determined by the capacitance of the capacitor (C) connected to the PWM pin.

 $f_{PWM} \approx 1/(43000 \times C)$ 

If a 680pF capacitor is used, the circuit will oscillate at about 34kHz. If the PWM frequency is too low the motor will emit switching noise, and if it is too high the power loss in the output will increase. A frequency in the range 15kHz to 50kHz is desirable. This capacitor must be connected between this pin and the GND pin by lines that are as short as possible to make this circuit immune to noise.

The capacitor ground side must be connected as close as possible to the IC control block ground (the GND1 pin), to minimize the influence of the output.

#### 7. Hall sensor input signals

The Hall sensor input signals must have an amplitude (differential) of over 50mVpp. If disruption of the output waveforms occurs due to noise on these signals, capacitors must be connected between the Hall sensor inputs (between the + and - sides).

#### 8. FCS pin

The capacitor (about  $0.1\mu F$ ) connected to the FC pin is required for correction of the control loop frequency characteristics.

## 9. Constraint protection circuit

The LB11873 includes a built-in constraint protection circuit to protect the IC and the motor if the motor is physically constrained from turning.

If FG signal (one side edge of IN1) does not switch states for a period in excess of a certain fixed time in the start state, the PWM drive side output is turned off.

The time is set by the capacitor connected to the CSD pin.

Set time (seconds)  $\approx 30.5 \times 0.98 \times CCSD (\mu F)$ 

If a 0.033μF capacitor is used, the protection operation time will be about 0.99 seconds.

The constraint protection state can be cleared by either switching to the stop state (and remaining for over 100µs) or turning the power off and then on again. Note that the constraint protection circuit may not operate correctly if there is noise on the FG signal when the motor is physically constrained.

#### 10. Phase lock signal

#### (1) Phase lock range

Since this IC does not have a speed system counter, the speed error range in the phase locked state cannot be determined by the IC characteristics alone. (This is because the range is affected by the acceleration with changes in the FG frequency.) If it is necessary to stipulate this in conjunction with a motor, it will be necessary to measure the range with the actual motor state. Since speed errors occur easily in states where the FG acceleration is large, it is thought that the lock pull-in time at startup and the unlock time due to clock switching will be the cases where the speed error is the largest.

## (2) Phase lock signal mask function

It is possible to assure that the lock signal is output in stable states by masking the short-term low levels due to hunting during lock pull-in. Note, however, that the lock signal output will be delayed by the amount of the mask time.

The mask time is set by the capacitor connected between the CLD pin and ground.

Mask time (s)  $\approx 6.5 \times 0.98 \times CCSD (\mu F)$ 

When a  $0.033\mu F$  capacitor is used, the mask time will be about 210ms. If full masking is required, the mask time must be set with an adequate margin.

#### 11. Initial reset

To apply an initial reset to the logic circuit, the IC goes to the reset state until the CSD pin voltage changes from 0V to about 0.63V. After the reset is cleared, drive will start. The reset time can be calculated quite closely with the following equation.

Reset time (s)  $\approx 0.13 \times CCSD (\mu F)$ 

A reset time of over 100µs is required.

## 12. Power supply stabilization

Since this IC is used in switching drive applications with large output currents, the power supply line is easily disrupted.

Therefore it is necessary to connect an adequately large capacitor between the V<sub>CC</sub> pin and ground.

The capacitor ground side is connected to the GND2 pin, which is the power system ground, and must be connected as close as possible to the pin.

If the capacitor (an electrolytic capacitor) cannot be connected close to the pin, a ceramic capacitor of about  $0.1\mu F$  must be connected close to the pin.

If reverse control mode (torque braking) is selected for braking, since there will be states where the current returns to the power supply, the power supply line level will be especially subject to disruption. Since the power supply line is most easily disrupted during lock pull-in at high speeds, designers must analyze this case carefully and select an adequately large capacitor.

Since the power supply line is particularly susceptible to disruption if a diode is inserted in the power supply line to prevent destruction of the IC by reverse connection, an even larger capacitor must be selected in this case.

## 13. VREG stabilization

Connect a capacitor with a value over  $0.1\mu F$  to stabilize the VREG voltage, which is the IC's control circuit power supply. This capacitor's ground side must be connected as close as possible to the IC's control block ground (the GND1 pin).

#### 14. Error amplifier system components

The external components for the error amplifier block must be located as close as possible to the IC to minimize the influence of noise. These components must also be located as far from the motor as possible.

## 15. FRAME pin

An electrolytic capacitor must be connected between the FRAME pin and GND2 with the capacitor's ground side is connected to GND2.

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